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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known		
				Application Number	Based on SN 10/035,441	
				Filing Date	Filed: January 4, 2002	
				First Named Inventor	Naoaki YAMAGUCHI et al.	
				Group Art Unit	1765	
Examiner Name	Anita Karen Alanko					
Attorney Docket Number	0756-7191					
Sheet	1	of	3			

U.S. PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Office ²	Number ⁴	Kind Code ⁵ (if known)				
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
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Examiner Signature	<i>Calvin U</i>	Date Considered	6.20.05
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		Number	Kind Code ² (if known)			
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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CL		A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," USSR, pp. 635-640, Phys. Stat. Sol. (A) Vol. 95, 1986.	
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Examiner Signature	<i>calomlu</i>	Date Considered	6.30.05
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CL		G. Liu, S.J. Fonash, "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low Temperature Processing," Appl. Phys. Lett 62 (20), May 17, 1993, 1993 American Institute of Physics, pp. 2554-2556.	
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Examiner Signature	<i>catomlu</i>	Date Considered	6.20.05
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